

ABSTRACT OF THE DISCLOSURE

A rework process of patterned photo-resist layer is provided. First, a substrate is provided with a first DARC, a first primer and a first patterned photo-resist layer being sequentially formed thereon. Next, remove the first
5 patterned photo-resist layer and the first primer from the first DARC. After that, form a second DARC on the first DARC; form a second primer on the second DARC. Last, form a second patterned photo-resist layer on the second primer.

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